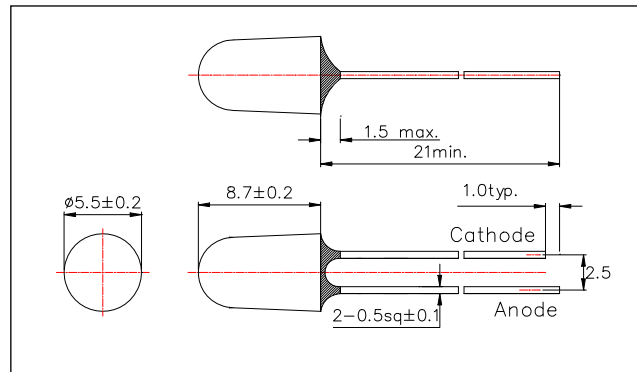


L735-06-55
Infrared LED Lamp

<Specifications>

- Chip Material: AlGaAs
- Chip Dimension: 550um x 550um
- Number of Chips: 1pcs
- Peak Wavelength: 735nm typ
- Package Type: Φ5mm Clear Molding
- Lead Frame: Soldered(Lead Free)
- Lens: Epoxy Resin

Outer Dimension (Unit:mm)



Absolute Maximum Ratings[Tc=25°C]			
Item	Symbol	Maximum Rated Value	Unit
Power Dissipation	PD	170	mW
Forward Current	IF	100	mA
Pulse Forward Current*	IFP	1000	mA
Reverse Voltage	VR	5	V
Thermal Resistance***	Rthja	240	K/W
Junction Temperature	Tj	100	°C
Operating Temperature	TOPR	-40 ~ +85	°C
Storage Temperature	TSTG	-40 ~ +100	°C
Soldering Temperature**	TSOL	265	°C

* Duty 1% and Pulse Width=10us.

** Soldering condition must be completed within 3 second at 265°C.

*** : junction - ambient, leads 7mm, soldered on PCB.

Electro-Optical Characteristics[Ta=25°C]						
Item	Symbol	Condition	Min	Typ	Max	Unit
Forward Voltage	VF	IF=50mA		1.6	1.7	V
	VFP	IPF=1A		3.5		
Total Radiated Power*	PO	IF=50mA	13	18		mW
Radiant Intensity**	IE	IF=20mA		110		mW/sr
	IEP	IPF=1A		2200		
Peak Wavelength	λP	IF=50mA	720	735	750	nm
Half Width	Δλ	IF=50mA		35		nm
Viewing Half Angle	θ1/2	IF=50mA		±8		deg
Rise Time	tr	IF=50mA		80		ns
Fall Time	tf	IF=50mA		80		ns

* Measured by Photodyne #500

** Measured by Tektronix J-6512

